

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 06-125013

(43)Date of publication of application : 06.05.1994

(51)Int.Cl.

H01L 21/90
H01L 21/285
H01L 21/3205

(21)Application number : 05-077697

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(22)Date of filing : 11.03.1993

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(30)Priority

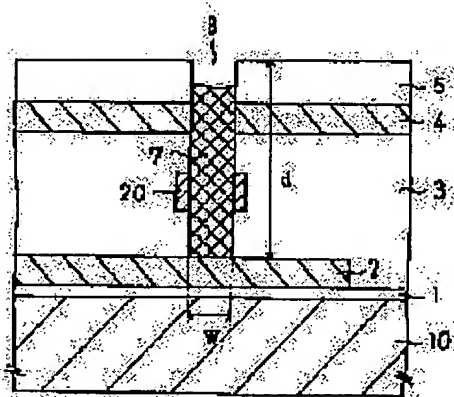
Priority number : 04 89591 Priority date : 14.03.1992 Priority country : JP

(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

(57)Abstract:

PURPOSE: To provide a structure for semiconductor device which is excellent in electric characteristics and can cope with an increase in degree of integration and a semiconductor device manufacturing method by which a semiconductor device having a multilayer interconnection structure can be manufactured through a simple manufacturing process.

CONSTITUTION: On a semiconductor substrate 10, an upper-layer wiring 4 is formed on a lower-layer wiring 2 with at least one layer insulating film 3 in between and an upper insulating film 5 is formed so as to coat the wiring 4. Then dummy wiring 20 is inserted between the upper- and lower-layer wiring. A contact hole 9 is formed against the upper- and lower-layer wiring including the dummy wiring from the top of the insulating film 5 and the hole 9 is filled with connecting wiring 7. The connecting wiring 7 surely provides electrical connection between the upper and lower-layer wiring.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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